Medium power Transistor(-32V, -2A) 2SB1188/2SB1182/2SB1240/2SB891F/ 2SB822/2SB1277/2SB911M

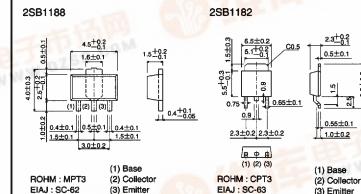
Features

- 1) Low VCE(sat). $V_{CE(sat)} = -0.5V (Typ.)$ $(I_C/I_B = -2A/-0.2A)$
- 2) Complements the 2SD1766/ 2SD1758/2SD1862/2SD1189F/ 2SD1055/2SD19192/SD1227M.
- Structure

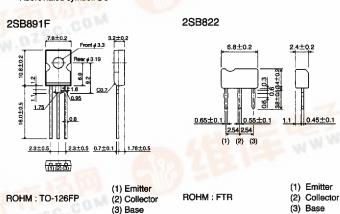
Epitaxial planar type PNP silicon transistor

2SB1240

External dimensions (Units: mm)



Abbreviated symbol: BC *



(2) Collector ROHM: ATV (3) Base 2SB1277

2.54 2.54

1.1 0.45±0.1 (1) Emitter (2) Collector (3) Base

(1) Emitter

ROHM: ATR EIAJ: SC-71 (3) Base

2SB911M

BOHM: FIL

Bi-polar transistor

●Absolute maximum ratings (Ta = 25°C)

Para	ameter	Symbol	Limits	Unit
Collector-base v	roltage	Vсво	-40	V
Collector-emitte	r voltage	VCEO	-32	V
Emitter-base vo	Itage	VEBO	-5	V
0-111			-2	A (DC)
Collector curren	I	lc	-3	A (Pulse) *1
	2SB1188		0.5	144
			2	- W *2
	2SB1182		10	W(Tc=25℃)
Collector power dissipation	2SB1240,2SB911M	Pc	1	*3
uissipation	20D004E	2SB891F	1.2	- w -
	2300917		5	W(Tc=25℃)
	2SB822,2SB1277		0.75	w
Junction temper	ature	Tj	150	Ĉ
Storage tempera	ature	Tstg	-55~150	r

^{*1} Single pulse Pw=100ms

●Electrical characteristics (Ta = 25°C)

Pa	rameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base	breakdown voltage	ВУсво	-40	_	_	٧	Ic=-50 μA
Collector-emitte	er breakdown voltage	BVCEO	-32			٧	Ic=-1mA
Emitter-base bi	reakdown voltage	ВУЕВО	-5	_	_	٧	I _E =-50 μ A
Collector cutoff	current	Ісво		_	-1	μΑ	V _{CB} =-20V
Emitter cutoff c	urrent	IEBO			-1	μΑ	V _{EB} =-4V
Collector-emitte	er saturation voltage	VCE(sat)	_	-0.5	-0.8	٧	Ic/I _B =-2A/-0.2A *
DC current	2SB1188,2SB1182 2SB1240,2SB891F	82		390		*	
transfer ratio	2SB822,2SB1277 2SB891F	hfE	120	_	390		Vc=-3V, lc=-0.5A
Transition frequ	iency	fτ	_	100	_	MHz	Vc=-5V, l==0.5A, f=30MHz
Output capacita	ance	Cob		50	_	pF	VcB=-10V, IE=0A, f=1MHz

^{*} Measured using pulse current.

^{*2} On 40 x 40 x 0.7 mm ceramic board is used.

^{*3} Printed circuit board 1.7mm thick, collector copper plating 1cm² or larger.

●Packaging specifications and hre

		Package	Taping				Bulk	
		Code	T100	TL	TU2	TL2		
Туре	hre	Basic ordering unit (pieces)	1000	2500	2500	2500	1000	2000
2SB1188	PQF	٠ ٦	0	_	_		_	_
2SB1182	PQF	₹	-	0	_	_		<u> </u>
2SB1240	QR			_	0	_	_	
2SB891F	PQF	٦	_	_	_	_	0	_
2SB822	Q		_	_	_		_	0
2SB1277	Q		_	_	_	0	_	<u> </u>
2SB911M	Q		_	_	-	_		0

hre values are classified as follows:

Item	Р	Q	R
hre	82~180	120~270	180~390

Electrical characteristic curves

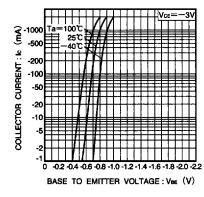


Fig.1 Grounded emitter propagation characteristics

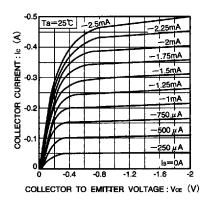


Fig.2 Grounded emitter output characteristics

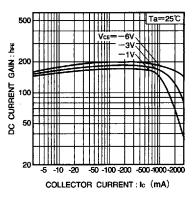


Fig.3 DC current gain vs. collector current (I)

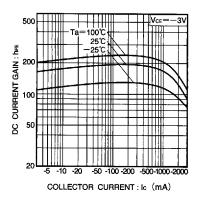
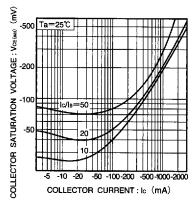
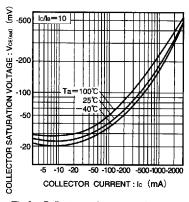


Fig.4 DC current gain vs. collector current (I)



Collector-emitter saturation voltage vs. collector current (I)



Collector-emitter saturation Fig.6 voltage vs. collector current (II)

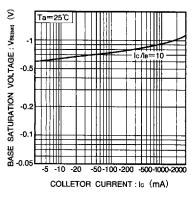


Fig.7 Base-emitter saturation voltage vs. collector current

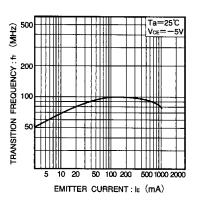
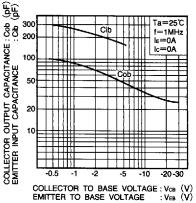
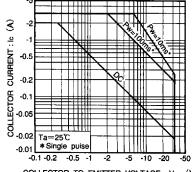


Fig.8 Gain bandwidth product vs. emitter current

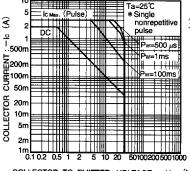


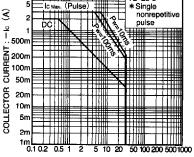
Collector output capacitance vs. collector-base voltage Emitter input capacitance vs. emitter-base voltage

Ta=25°C



COLLECTOR TO EMITTER VOLTAGE: VOE (V)





COLLECTOR TO EMITTER VOLTAGE: $-V_{\text{CE}}$ (V) COLLECTOR TO EMITTER VOLTAGE: $-V_{\text{CE}}$ (V)

Fig.10 Safe operation area (2SB1188)

Fig.11 Safe operation area (2SB1182)

Fig.12 Safe operation area (2SB891)

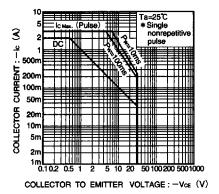


Fig.13 Safe operation area (2SB891 (TO-126M))

Packages

ROHM has been manufacturing transistors since 1975. In the development of products, we constantly strive to anticipate the needs of our customers. Regarding packages, the demands of the market for compactness, low power consumption, low power dissipation and automatic mounting support are becoming ever greater, and we are strengthening our product development system to meet these needs.

●Types and features of surface-mount packages

Туре	External dimensions (Units : mm)	Features
EMT3 SC-75A type	1.6±0.2 1.0±0.1 0.2±0.1 0.2±0.1 0.2±0.1 0.1±0.55 0.1±0.55 0.1±0.05	A more compact version of the UMT3 (SC-70), the EMT3 is the world's smallest transistor with a mold size of 1.6 × 0.8 mm. The mounting area is approximately 60% of the UMT3 and 30% of the SMT3, making it ideal for ultra-high density mounting. Mounting is possible with the same type of automatic mounting machine as the UMT3.
UMT3 SC-70 type	2.0±0.2 1.3±0.1 0.65 0.65 0.2 0.7±0.1 0.3±0.1 0.15±0.05 0.15±0.05	The UMT3 is a smaller version of the SMT3 (SC-59). The mounting area is approximately 60% of the SMT3, making it optimum for high density mounting. The taping size is the same as the SMT3, allowing use of conventional automatic mounting machines. Electrical characteristics and reliability are the same as the SMT3.
SMT3 SC-59 type	2.9±0.2 1.9±0.2 0.950.95 0.8±0.1 0~0.1 All terminals have same dimensions 0.4+0.1 0.15 0.15 0.06 0.15 0.06 0.15 0.06 0.15 0.06 0.15 0.06 0.15 0.06 0.15 0.06 0.15 0.06 0.15 0.06 0.15 0.15 0.06	The SMT3 is a compact package suitable for small electronic devices and hybrid IC applications. With proven performance, this is one of the most basic small packages. With the exception of Pc (collector power dissipation), electrical characteristics are similar to leaded packages. Reliability is on the same level as the TO-92.
MPT3 SC-62 type	4.5-0.2 1.8±0.1 1.5±0.1 1.5±0.1 1.5±0.1 1.5±0.1 1.5±0.1 1.5±0.1	By itself the MPT3 has a Pc of 0.5 W (Ta = 25°C), but when used on a 40 × 40 × 0.7 mm ceramic board, Pc = 2 W (Tc = 25°C), allowing high power to be obtained with a small package. The flat package makes it suitable for applications requiring compactness such as hybrid ICs. Available on tape for automatic mounting.

T		
Туре	External dimensions (Units : mm)	Features
CPT 3 SC-63 type	0.75 0.85±0.1 0.75 0.85±0.1 0.55±0.1 0.55±0.1 0.55±0.1 0.55±0.1 0.55±0.1	By itself the CPT3 has a Pc of 1 W (Ta = 25°C), but a large Pc of several watts can be obtained with an appropriate mounting surface. At the same time the CPT3 is compact, making it suitable for high density mounting and hybrid ICs. Available on tape for automatic mounting. For vertical high density mounting, the leaded CPT (SC-64) type with the same mold size is also available.
PSD3	10.1±0.3 10.1±0.3 1.3 0~0.3 1.3 0~0.3 1.3 0~0.3 1.3 0~0.3 1.3 1.3 0~0.3	The PSD3 is a TO-220 class surface-mount package. A high Pc can be obtained with an appropriate mounting surface. Surface mounting allows a high vertical density, enabling the design of slim and compact devices. The PSD3 is available on tape for automatic mounting, and it helps improve mounting efficiency and reduce mounting cost.
SMT5 SC-74A type	2.9±0.2 1.1+0.2 1.9±0.2 0.95 0.95 0.8±0.1 0.05 0	The SMT5 consists of two connected transistors or digital transistors in an SMT3 (SC-59) package. The mounting area can be reduced by 50% compared to the SMT3 and the internal circuitry is complete, making this package ideal for high density mounting at half the assembly cost.
SMT6 SC-74 type	2.9±0.2 1.9±0.2 0.950.96 0.8±0.1 0.00-0.1 0.15±0.1 0.15±0.1 0.15±0.1 0.15±0.1 0.15±0.1 0.15±0.1	The SMT6 consists of two independent transistors or two independent digital transistors in an SMT3 (SC-59) package. The mounting area and mounting cost can be reduced by 50% compared to the SMT3, and the two transistors are independent to allow free configuration of a high density circuit.

Туре	External dimensions (Units : mm)	Features
UMT5 SC-88A type	2.0±0.2 1,3±0.1 0,85 0,85 0,7 0,85 0,85 0,7 0,7 0,005 All terminals have same dimensions	The UMT5 consists of two connected transistors or digital transistors in a UMT3 (SC-70) package. The mounting area can be reduced by 50% compared to the UMT3 and the internal circuitry is completed, making this package ideal for high density mounting at half the assembly cost.
UMT6 SC-88 type	2.0±0.2 1,3±0.1 0.65 0.65 0.7 0.7 0.7 0.7 0.7 0.7 0.7 0.7	The UMT6 consists of two independent transistors or two independent digital transistors in a UMT (SC-70) package. The mounting area and mounting cost can be reduced by 50% compared to the UMT3, and the two transistors are independent to allow free configuration of a high density circuit.

Types	and f	eatures	of I	eaded	packages
TIVE	anui	calules	UI I	caucu	Dathaues

Туре	External dimensions (Units : mm)	Features
SPT (SC-72 type)	2±0,2 0.45±0.15 0.45±0.15 0.5 0.45±0.15	The SPT is a smaller version of the conventional TO-92 type. The body size (3×4×2 mm³) has been reduced to 1/4 that of the TO-92 (5×5×4 mm³). The SPT is available on tape for automatic insertion, and less space is occupied on the printed circuit board than the TO-92. Reliability is the same as the TO-92.
FTR	0.65±0.1 2.4±0.2 0.65±0.1 0.65±0.1 0.65±0.1 0.45±0.1	SIL type with a height of 3.4 mm and a lead pitch of 2.54 mm.
FTL	0.65Max 0.65Max 0.5±0.1 0.5±0.1 0.45±0.1	The FTL is a radial taping version of the highly popular FTR. This enables automatic high-density mounting with a radial insertion machine.
ATR (SC-71 type)	0.65Max 0.45±0.1	SC-71type with a height of 4.4 mm and a Pc=1W type.

Туре	External dimensions (Units : mm)	Features
ATV	0.65Max 0.5±0.1 2,5±0.2 0.65Max 0.5±0.1 0.45±0.1	The ATV is a radial taping version of the highly popular ATR. This enables automatic high-density mounting with a radial insertion machine.
TO-92 (SC-43 type)	4.8±0.2 3.7±0.2 0.5±0.1 2.5±0.3 5 0.45±0.1 2.3	The SC-43 is for general purpose small signals.
TO-126FP	7.8±0.2 Front ±3.3 Reer ≠3.18 Co.7 Co.7 Co.7 Co.7 Co.7 Co.7 Co.7 Co.7	The TO-126FP is an isolation type package based on a TO-126 full mold. In addition to the features of the TO-126, molded heat sink fins allow easy isolation of the heat sink.
TO-220FP (SC-67 type)	70+0.1 70+0.3 70+0.3 70+0.3 70+0.3 70+0.3 70+0.3 70+0.1	The TO-220FP is an isolation type package based on a TO-220 full mold. In addition to the features of the TO-126 and TO-220, molded heat sink fins allow easy isolation of the heat sink.

Туре	External dimensions (Units : mm)	Features
TO-220FN	10.0 ±0.3 0.3 ±0.2 0.3 ±0.2 0.4 ±0.2 0.4 ±0.2 0.7 ±0.3 0.7 ±	The TO-220FN features the same performance as the TO-220FP with approximately 2 mm less height, allowing the design of slimmer devices. Furthermore, the elimination of support pins in the fin (collector electrode) solves short-circuiting problems with neighboring components and the chassis. To make the height to the installation hole the same as the TO-220FP, it can be replaced as is from the TO-220FP.